



TP0101K vs. TP0101T

Description: P-Channel,20-V (D-S) MOSFET, Low Threshold
Package: SOT-23
Pin Out: Identical

Part Number Replacements:

TP0101K-T1-E3 Replaces TP0101T-T1-E3
TP0101K-T1-E3 Replaces TP0101T-T1

Summary of Performance:

The TP0101K is a technology upgrade with ESD protection to the original TP0101T. The ESD protection diodes on the gate increases Gate-Body Leakage; otherwise, there is little variation regarding performance.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)								
Parameter	Symbol	TP0101K		TP0101T		Unit		
Drain-Source Voltage	V_{DS}	-20	-20				V	
Gate-Source Voltage	V_{GS}	± 8	± 8					
Continuous Drain Current	I_D	-0.58	-0.6				A	
		-0.46	-0.48					
Pulsed Drain Current	I_{DM}	-2	-3					
Continuous Source Current (MOSFET Diode Conduction)	I_S	-0.3	-0.6					
Power Dissipation	P_D	0.35	0.35				W	
		0.22	0.22					
Operating Junction & Storage Temperature Range	T_J & T_{stg}	-55 to 150		-55 to 150		°C		
Maximum Junction-to-Ambient	R_{thJA}	357		357		°C/W		

SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)								
Parameter	Symbol	TP0101K			TP0101T			Unit
		Min	Typ	Max	Min	Typ	Max	
Static								
Gate-Threshold Voltage	$V_{GS(th)}$	-0.5	-0.7	-1.0	-0.5	-0.9	-1.5	V
Gate-Body Leakage	I_{GSS}			± 5000			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}			-1			-1	μA
On-State Drain Current	$I_{D(on)}$	-1.2			-2.5			A
		-0.5			-0.5			
Drain-Source On-Resistance	$r_{DS(on)}$	0.42	0.65		0.45	0.65		Ω
		0.64	0.85		0.69	0.85		
Forward Transconductance	g_{fs}	1300			1300			S
Diode Forward Voltage	V_{SD}	-0.9	-1.2		-0.9	-1.2		V
Dynamic								
Total Gate Charge	Q_g	1400	2200		2020	3000		nC
Gate-Source Charge	Q_{gs}	300			180			
Gate-Drain Charge	Q_{gd}	250			720			
Gate Resistance	R_g	150			NS			Ω
Switching^a								
Turn-On Time	$t_{d(on)}$	25	35		7	12		ns
	t_r	30	45		25	35		
Turn-Off Time	$t_{d(off)}$	55	85		19	30		
	t_f	38	60		9	15		

NS denotes not specified in original datasheet